| Substitute for Form 1449 A & B/PTO | | | | Complete if Known | | | |
|------------------------------------|----------------|----------------|------|------------------------|------------------|---|--|
| Substitute for Form 1 | 449 A & D/FIU | | | Application Number | 10/050,570 | _ | |
| INFO | DRMATION | N DISCLOS | SURE | Confirmation Number | 7078 | | |
| STATEMENT BY APPLICANT | | | | Filing Date | January 18, 2002 | | |
|)'' & \ | | | | First Named Inventor | Kuniaki YAGI | | |
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| P 2 5 2003 🛂 🔼 | | | | Examiner Name | SONG, MATTHEW | _ | |
| Sh | 1 | of | 1 | Attorney Docket Number | Q68148 | | |

| TRADEMAR | RADEMARIE U.S. PATENT DOCUMENTS | | | | | | |
|-----------------------|----------------------------------|--------------|-----------------------------------|--------------------------------|-------------------------------------------------|--|--|
| Examiner Initials* | Cite No.1 | Document | | Publication Date MM-DD-YYYY | | | |
| | | Number | Kind Code ¹ (if known) | | Name of Patentee or Applicant of Cited Document | | |
| M2 | | US 5,225,032 | Α | 07-06-1993 | Golecki | | |
| | | US | | | RECEIVED | | |
| | | US | | | | | |
| | | US | | | SEP 3 () 2003 | | |
| | | US | | | JEI 3 | | |
| | _ | US | | | TC 1700 | | |
| | | US | | | 10 1700 | | |
| | | US | | | | | |
| | | US | | | | | |

| | FOREIGN PATENT DOCUMENTS | | | | | | | |
|---------------------------------|--------------------------|------------------------------|---------------------|-----------------------------------|------------------|-----------------------------|--------------------------|--|
| Examiner Cite Initials* No.1 | Cite | Foreign Patent Document | | | Publication Date | Name of Patentee or | | |
| | | Country Code ³ | Number ⁴ | Kind Code ⁵ (if known) | MM-DD-YYYY | Applicant of Cited Document | Translation ⁶ | |
| Mi | | EP , | 1 179 620 | Al | 02-13-2002 | Nagasawa | | |
| | | EP ' | 1 160 361 | A1 | 12-05-2001 | Nagasawa et al. | | |
| | | EP 、 | 0 632 145 | A2 | 01-04-1995 | Loboda | | |
| M3 | | EP , | 0 639 661 | A2 | 02-22-1995 | Loboda et al. | | |
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| Examiner Initials* | Cite No.1 | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published. | Translation |
|-----------------------|--------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------|
| M | • | BJÖRKETUN, LO. et al., "Interfacial Void Formation During Vapor Phase Growth of 3C-SiC on Si(0 0 1) and Si (1 1 1) Substrates Characterization by Transmission Electron Microscopy," Journal of Crystal Growth, December 1997, pp. 379-388, Vol. 182, No. 3-4, North-Holland Publishing Co., Amsterdam, NL. | |
| MS | • | YAGI, K. et al., "3C-SiC Growth By Alternate Supply of SiH ₂ Cl ₂ and C ₂ H ₂ ," Journal of Crystal Growth, April 1997, pp. 653-657, Vol. 174, No. 1-4, North-Holland Publishing Co., Amsterdam, NL. | |
| m | 1 | STECKL, A.J. et al., "Epitaxial Growth of β-SiC on Si by RTCVD with C ₃ H ₈ and SiH ₄ ," IEEE Transactions on Electron Devices, January 1992, pp. 64-74, Vol. 39, No. 1, IEEE Inc., New York, US. | |
| | | | |

Examiner Signature Date Considered 3/1/2004

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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